

General Description:

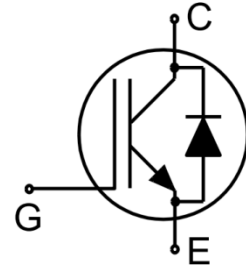
Using RST's proprietary trench design and advanced FS (Field Stop) second generation technology, the 650V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology offering
- Very low $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
RST80TD65BP	TO-3P	RST80TD65BP



TO-3P

Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate- Emitter Voltage	± 30	V
I_C	Collector Current	160	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	80	A
I_{Cplus}	Pulsed Collector Current, t_p limited by T_{jmax}	240	A
-	turn off safe operating area, $V_{CE}=650\text{V}$, $T_j=150^{\circ}\text{C}$	240	A
I_F	Diode Continuous Forward Current @ $T_C = 100^{\circ}\text{C}$	80	A
I_{FM}	Diode Maximum Forward Current	240	A
P_D	Power Dissipation @ $T_C = 25^{\circ}\text{C}$	390	W
	Power Dissipation @ $T_C = 100^{\circ}\text{C}$	195	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering	260	$^{\circ}\text{C}$
t_{sc}	Short circuit withstand time $V_{GE}=15\text{V}$, $V_{CC}\leq 400\text{V}$, Allowed number of short circuits<1000Time between short circuits: $\geq 1.0\text{s}$, $T_j\leq 150^{\circ}\text{C}$	5	us

Thermal Characteristic

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.38	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	1.41	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

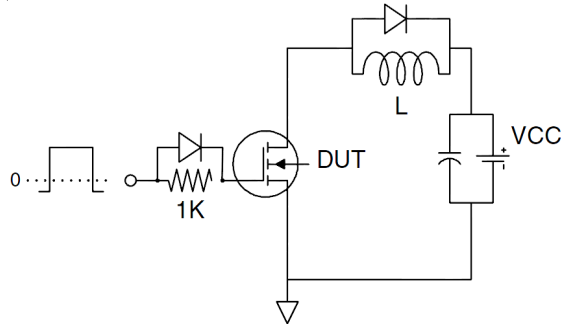
Symbol	Parameter	Test Conditions		Value			Units
				Min.	Typ.	Max.	
Static Characteristics							
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V,I _{CE} =1mA		650	--	--	V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V,V _{CE} =650V		--	--	6	uA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30V,V _{CE} =0V		--	--	200	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30V,V _{CE} =0V		--	--	200	nA
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =80A	T _J =25°C	--	1.7	1.9	V
		V _{GE} =15V	T _J =150°C	--	1.9	--	V
V _{GE(th)}	Gate Threshold Voltage	I _C =1mA,V _{CE} =V _{GE}		4.0	5.0	6.0	V
Dynamic Characteristics							
C _{ies}	Input Capacitance	V _{CE} =25V,V _{GE} =0V, f=1MHz		--	9188	--	pF
C _{oes}	Output Capacitance			--	258	--	
C _{res}	Reverse Transfer Capacitance			--	181	--	
Q _g	Total Gate Charge	V _{CC} =480V, I _C =80A V _{GE} =15V		--	331	--	nC
Q _{ge}	Gate to Emitter Charge			--	74	--	
Q _{gc}	Gate to Collector Charge			--	136	--	
I _{C(SC)}	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V _{GE} =15V,V _{CC} ≤400V, t _{sc} ≤5us,T _J ≤150°C		--	450	--	A
Switching Characteristics							
t _{d(ON)}	Turn-on Delay Time	V _{CC} =400V,I _C =80A V _{GE} =0/15V, R _g =5Ω Inductive Load		--	19	--	ns
t _r	Rise Time			--	17	--	
t _{d(OFF)}	Turn-Off Delay Time			--	172	--	
t _f	Fall Time			--	20	--	
E _{on}	Turn-On Switching Loss			--	1.43	--	mJ
E _{off}	Turn-Off Switching Loss			--	1.45	--	
E _{ts}	Total Switching Loss			--	2.88	--	

Electrical Characteristics of the Diode($T_c= 25^{\circ}\text{C}$ unless otherwise specified):

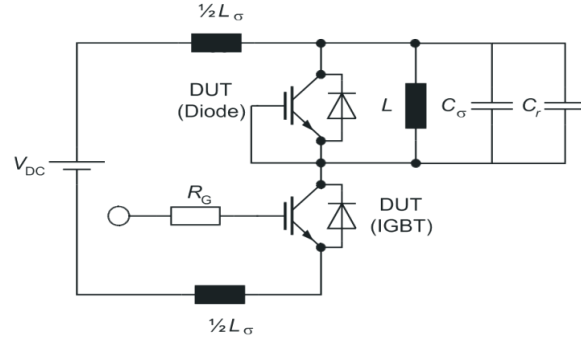
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{FM}	Diode Forward Voltage	I _F =80A	--	1.75	2.0	V
T _{rr}	Reverse Recovery Time	I _F =80A, di/dt=200A/us	--	194	--	ns
I _{RRM}	Diode Peak Reverse Recovery Current		--	2.8	--	A
Q _{rr}	Reverse Recovery Charge		--	0.2	--	uC
Pulse width t _{ip} ≤380μs,δ≤2%						

Test Circuit

1) Gate Charge Test Circuit

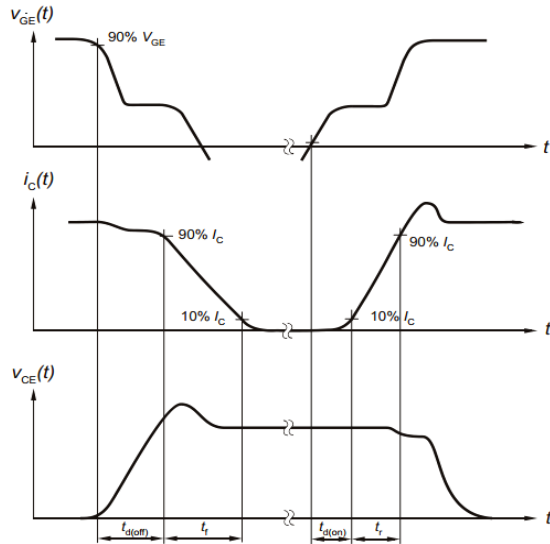


2) Switch Time Test Circuit

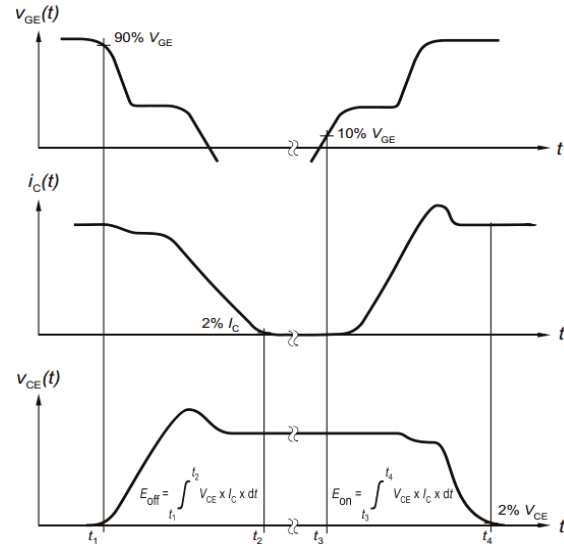


Switching characteristics

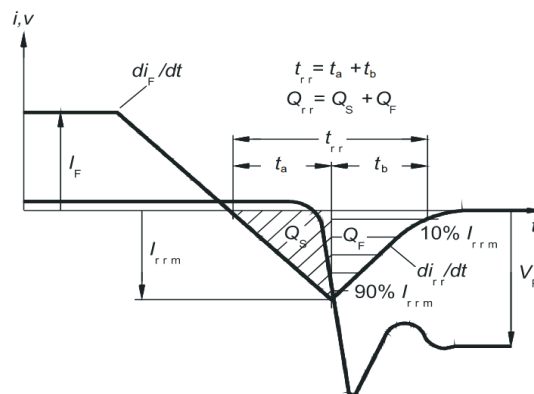
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

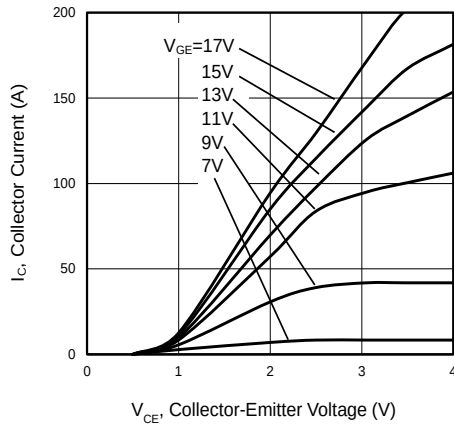


Figure 2 Transfer Characteristics

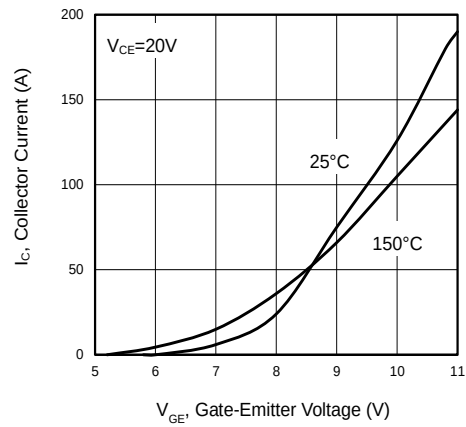


Figure 3 V_{CEsat} vs. Case Temperature

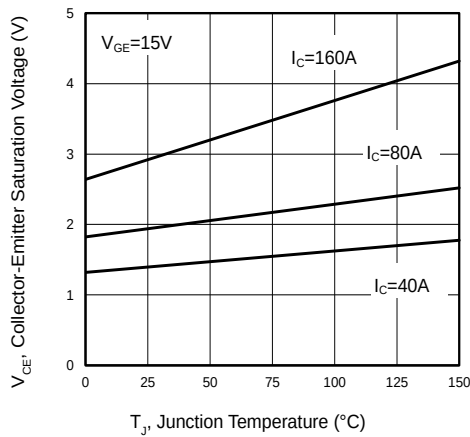


Figure 4 Saturation Voltage vs. V_{GE}

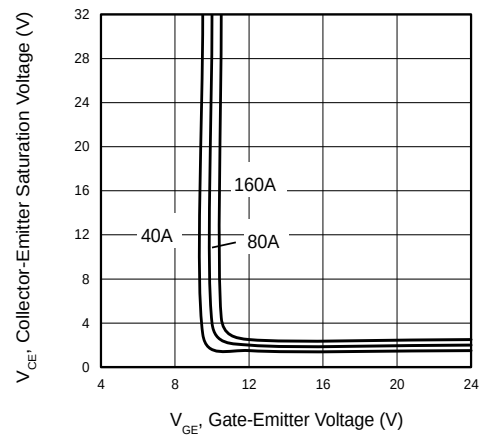


Figure 5 Capacitance Characteristics

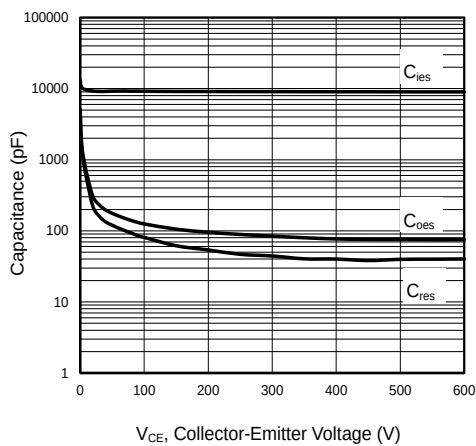
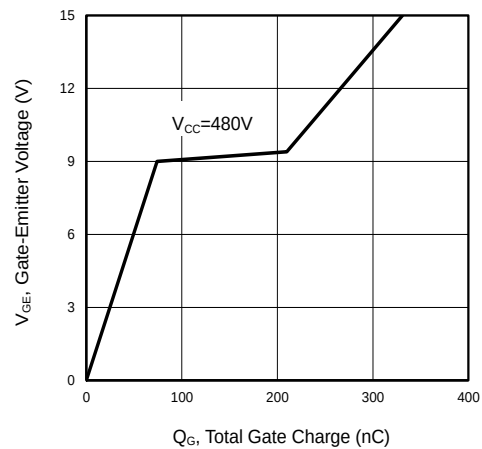


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics

Figure 7 Forward Characteristics

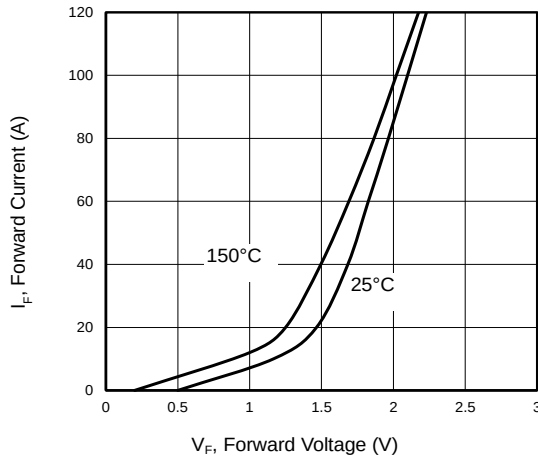


Figure 8 V_F vs. temperature

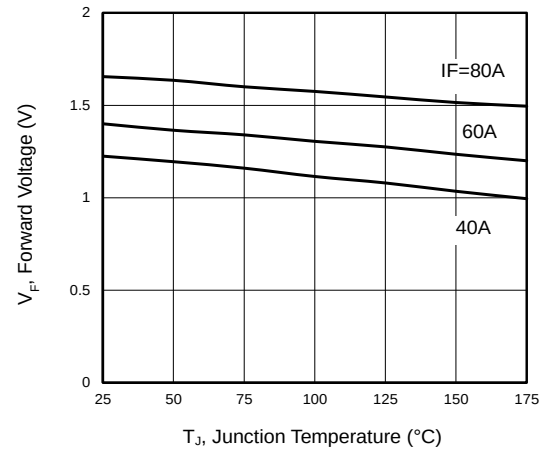


Figure 9 Typical Switching Times as a Function of Gate Resistor

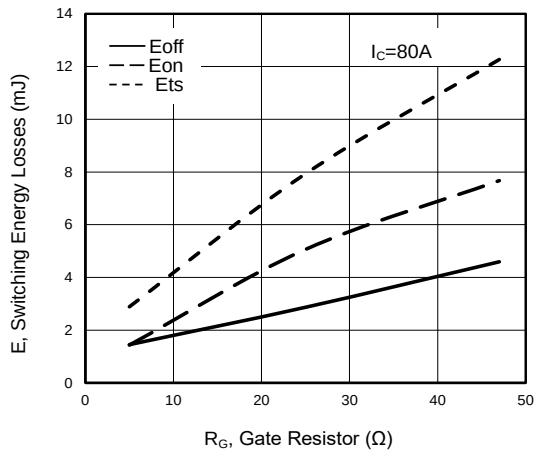


Figure 10 Typical Collector-emitter Saturation Voltage as a function of Collector Current

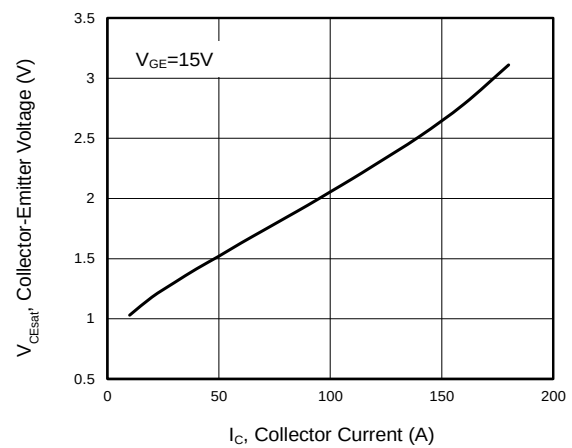


Figure 11 Gate-emitter Threshold Voltage as a Function of Junction Temperature

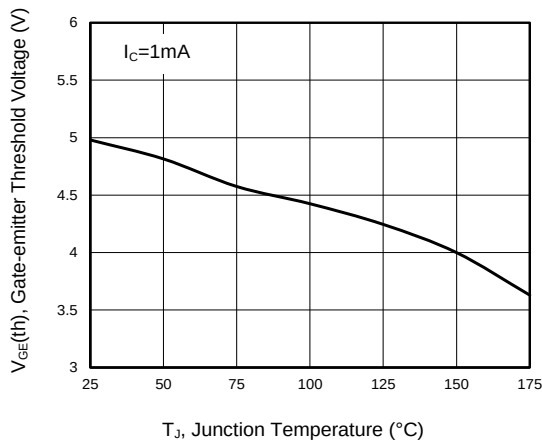
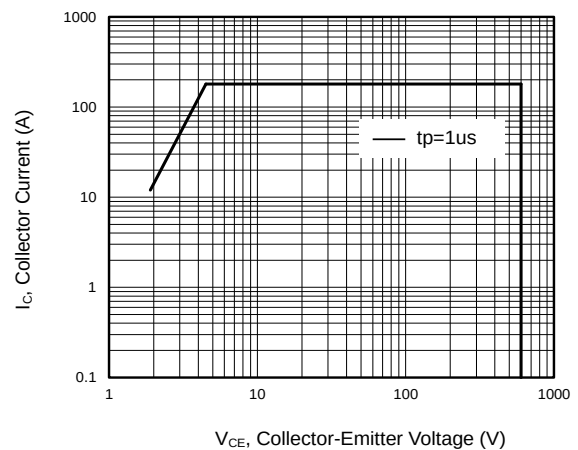
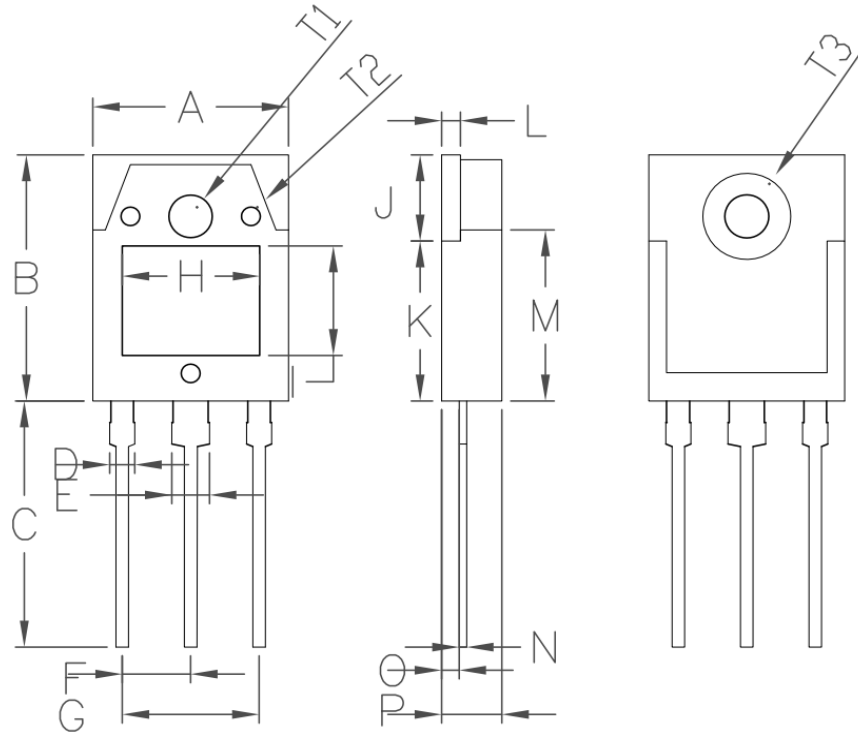


Figure 12 Forward Bias Safe Operating Area



TO-3P-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	15.50	15.70	0.61	0.62
B	19.70	20.10	0.78	0.79
C	20.10	20.50	0.79	0.81
D	2.00		0.08	
E	3.00		0.12	
F	5.45		0.21	
G	10.90		0.43	
H	10.80	11.00	0.43	0.43
I	8.80	9.00	0.35	0.35
J	6.85	7.15	0.27	0.28
K	12.75	13.05	0.50	0.51
L	1.49	1.51	0.06	0.06
M	13.70	14.00	0.54	0.55
N	0.59	0.61	0.02	0.02
O	1.32	1.48	0.05	0.06
P	4.70	4.90	0.19	0.19
T1	3.50		0.14	
T2	1.50		0.06	
T3	7.00		0.28	